Doping and Field-Induced Insulator-M etal Transitions in Half-D oped M anganites

O. Cepas,^{a,b} H. R. Krishnamurthy,^{a,c} and T. V. Ramakrishnan^{a,c,d}

Indian Institute of Science, Bangalore 560012, India.

c. Jawaharlal Nehru Centre for Advanced Scienti c Research, Jakkur, Bangalore 560 064, India.

d. Department of Physics, Banaras Hindu University, Varanasi 221005, India.

(D ated: M arch 22, 2024)

W e argue that m any properties of the half-doped m anganites m ay be understood in terms of a new two-(e_g electron)- uid description, which is energetically favorable at interm ediate Jahn-Teller (JT) coupling. This emerges from a competition between canting of the core spins of M n promoting m oble carriers and polaronic trapping of carriers by JT defects, in the presence of CE, orbital and charge order. We show that this explains several features of the doping and m agnetic eld induced insulator-m etal transitions, as the particle-hole asymm etry and the sm allness of the transition elds.

H alf-doped" m anganites such as R e_{1 x} A_x M nO₃ withx = 1=2 where Re is a 3+ rare-earth ion and A a 2+ alkaline earth ion have been the object of extensive studies for m any years [1]. The lowest tem perature phase seems to be either the CE phase, consisting of ferrom agnetic zigzag chains with relative antiferrom agnetic (AF) order (as in $La_{1=2}Ca_{1=2}M$ nO₃, where it was rst proposed [2, 3], and in $Nd_{1=2}Sr_{1=2}M nO_3$ [4] or $Nd_{1=2}Ca_{1=2}M nO_3$ [5]) or an A-type phase, i.e., ferrom agnetic planes with relative AF alignment (as in $Pr_{1=2}Sr_{1=2}M$ nO₃ [4]). The competition between the CE and A phases appears even in a sim ple one-orbitalm odel [6] because of the interplay of ferrom agnetic double-exchange and AF superexchange between the core $t_{2\alpha}$ spins of M n (see also Fig. 1). The presence of charge and orbital order as proposed by G oodenough [3] is more di cult to establish. X -ray di raction experim ents do suggest the presence of large Jahn-Teller (JT) distortions [4, 7] with two inequivalent M n sites. In the CE phase, the alternating $(3x^2)$ r^2)=(3 y^2 r²) orbitalorder (consistent with the observed distortions) was shown to optim ize the anisotropic hopping energy of the e_{α} electrons in a more realistic two e_{α} orbital model [8]. The origin of charge-order was attributed to on-site [8] or intersite Coulomb interactions [9, 10], though the latter tends to favor a Wigner crystal [9] rather than the charge stacked order found experimentally [1]. The role of the JT coupling has been investigated using imposed JT distortions [11] as well as by extensive classical M onte-C arlo simulations that lead to the observed charge stacked ordering [12].

However, several fundam ental issues remain to be understood. One of them is the striking asymmetry with respect to the addition of electrons or holes. Experimentally, added electrons typically favor ferrom agnetic metallic phases while added holes favor insulating phases [1]. In contrast, band structure arguments [8], and treatments including JT distortions adiabatically and classically [12] lead to metallic phases on both sides. A nother puzzling feature, rst seen in (N d,Sm)₁₌₂Sr₁₌₂M nO₃ [13] and later seen to be ubiquitous [1], is that magnetic elds

10 40 Tesla, which are extremely smallcompared with N eelor charge ordering temperatures 200 K, induce an insulator metal transition. This can be viewed as another manifestation of the colossal magneto-resistance (CMR) in doped manganites [1]. An explanation is that this arises from the proximity of the CE phase to a ferrom agnetic phase [6, 10, 14]; but it is di cult to understand why the parameters in so many systems should all be so nely tuned as to be near the phase boundary.

Recently, starting from a large JT coupling picture, a two-uid e_g electron model, one polaronic and localized, and the other band-like and mobile, was proposed and shown to explain, in particular, the CMR in the orbital liquid regime [15]. In this letter, we show how the two types of electrons can emerge from a realistic microscopic model, even at intermediate JT couplings, in the half-doped case where orbital and charge order have to be explicitly included. Basically, they arise from a competition between canting of the M n core spins promoting mobile carriers, and the JT coupling promoting polaronic, localized carriers. We show that our picture leads to natural explanations for the particle-hole asymmetry around half-doping as well as the magnetic-

eld-induced insulator-m etal transition at half-doping mentioned above. Interestingly, a similar two-carrier-type hypothesis was proposed based on phenom enological grounds in R ef. 16 to understand resistivity data in La_{1 x}C a_xM nO₃ (x 1=2); for which our theory provides a microscopic basis. JT distortions were recently tracked as function of eld in La₁₌₂C a₁₌₂M nO₃ and show n to play a crucial role near the eld-induced transition [17, 18]; our picture is completely consistent with this. We believe that the ideas presented here m ay be relevant to other classes of system s such as C sC ₆₀, in which a similar two-electron phase has been proposed [19].

Our theory is based on the following microscopic two-orbital H am iltonian for the manganites:

$$H [fS_{ia};Q_{ia}; i_{a}g] = \begin{array}{c} X \\ t_{abij}(S_{ia};S_{jb})c_{ia}^{y} c_{jb} \\ i_{j} ab \end{array}$$

a. Centre for Condensed Matter Theory, Department of Physics,

b. Institut Laue Langevin, BP 156, 38042 G renoble, France.

$$X X X + J_{AF}S_{ia} S_{b} g_{B} H S_{a}$$

$$\stackrel{\langle ia;jb>}{=} ia + \frac{1}{2}K Q_{ia}^{2} g Q_{ia} g Q_{ia}C_{ia}^{y} (ia)C_{ia}: (1)$$

Here $c_{i_{a}}^{y}$ creates an electron in the eg orbital (= y^2 , $3z^2$ r^2) in the unit cell i and a sublattice \mathbf{x}^2 site labelled by a. (W e use a 8-sublattice decomposition to accomm odate the CE phase.) There are N sites and dN electrons with c (1 x) close to 1=2. Due to a large H und's coupling J_{H} the electron spin is assumed to be locked parallel to the S = $3=2 t_{2g}$ core spins of M n, m odelled as classical vectors S_{ia}. The hopping param eters (with 4t=3 being the hopping between $(3z^2 r^2)$ orbitals in the z-direction) include the standard Anderson-H asegaw a dependence on ${\rm S}_{\,ia}\,\text{;}{\rm S}_{\,jb}$ that takes care of this large $J_{\rm H}$ projection [12]. The core spins are directly coupled by an AF superexchange, $J_{AF}S^2$ 0:1t [12]. H is the external magnetic eld. The last two terms include the vibrational energy of JT phonons (where K is the lattice sti ness of a sim pli ed non-cooperative m odel) and their coupling to the eq electrons. Q_{ia} and _{ia} represent the amplitude and the angle of the two $(Q_2; Q_3)$ JT modes, and the matrix the symmetry of their coupling [12]. On-site Coulomb interactions can be ignored in a rst approxim ation when large JT distortions are present (as the JT coupling suppresses double occupancy) and for large J_{H} .

W e have determ ined the ground state of (1) exactly num erically, but in the subspace of spin and distortion variables restricted to be periodic with a unit cell of at most 8 sites. This accommodates the CE state as well as several other com peting com m ensurate states. C om pared to earlier num erical approaches [12] that were lim ited to sm all clusters, our calculations are practically in the therm odynam ic lim it. W e con m the phase diagram that was previously obtained [12, 14] and obtain detailed predictions on the strength of the JT -distortions Q, etc. [20]. The phase diagram is given in Fig. 1 and the phases are described in the gure caption. The strong-coupling phases, all insulating and charge ordered, can be understood by starting from localized W annier orbitals centered on alternate JT distorted sites which are fully occupied. By virtual double exchange involving neighboring empty sites with aligned core spins [15], the electrons gain energy in a way that depends upon the orientation of the JT distortion or occupied orbital [20]. A comparison of the energies of the various phases leads to the sequence of rst-order transitions at couplings given by $J_{AF}S^2 = 4tK = (9g^2)$ and $J_{AF}S^2 = 8tK = (9g^2)$ (dotted dashed lines in Fig. 1).

Phases that are inhom ogeneous or incommensurate [21] can not be captured by the above analysis because of the limited size of the maximal unit-cell. We tackle this problem, albeit to a limited extent, by studying the

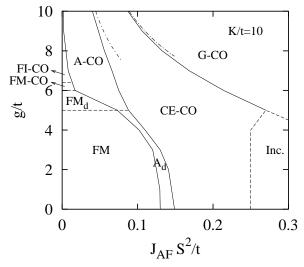


FIG.1: Phase diagram of the 3D two-orbital model (T = 0, x = 0.5, K =t = 10). FM (resp. FM_d): ferrom agnetic m etallic phase with no distortions (resp. sm all uniform distortions). FI-CO (resp. FM -CO): charge-ordered ferrom agnetic insulating (resp. m etallic) phase with distortions that favor occupancy of the x^2 y² orbitals. A_d: ferrom agnetic planes AF aligned with uniform distortions. A -CO: A with charge order. CE-CO: Ferrom agnetic zig-zag chains AF ordered, orbital ordered ($3x^2$ r²= $3y^2$ r² on the bridge sites), and charge-ordered (g=t > 0). G -CO: N eelAF phase with charge order. Inc.: incom m ensurate state that interpolates between CE and G.D otted dashed lines com e from analytical expressions derived in the strong-coupling lim it. Solid (dashed) lines show rst-order (second-order) phase transitions.

instabilities of the hom ogeneous insulating phases discussed above with respect to particle or hole excitations accompanied by single site defects in their JT distortion pattern. For this, we nd the electronic eigenvalues of (1) in the presence of such defects num erically (with N up to 1728), and calculate the energy cost or gain from lling the energy levels with cN electrons.

To start with, consider the FI-CO phase at strongcoupling, with the electrons localized at the JT distorted sites with distortion Q. If we now promote a particle across the charge gap, it is energetically favorable for the JT distortion at the hole site (from which the electron is rem oved) to relax to Q Q_d. The loss in electronic energy due to the scattering of the other electrons from the defect is overcom pensated by the gain in elastic energy. The hole gets polaronically trapped, while the electron is m obile. Such m ixed excitations thus have energies lower than the energies of particle-hole excitations due to band structure alone. For the FI-CO phase, this is demonstrated in Fig. 2 where, in addition to the minimum at $Q_d = 0$ (corresponding to the hom ogeneous phase), there is anotherm in imum at $Q_d = Q$, corresponding to the rem ovalof the JT distortion at one site. Furtherm ore, this minimum softens when q=t is reduced below q=t 6:8 (Fig. 2), although the other hom ogeneous phases of Fig.

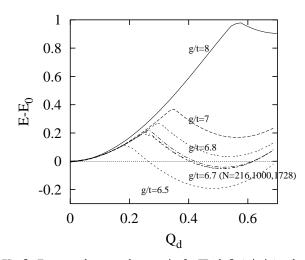


FIG.2: Energy change when a single JT defect is introduced in the FI-CO phase. Q Q_d is the JT distortion on a defect site; all the other occupied sites having the same distortion Q. The softening of the excitation with Q_d Q at g=t 6.8 signals a phase transition with proliferation of defects. Finitesize e ects are sm all and shown for g=t = 6.7.

1 are at higher energy at this g=t. The instability approach therefore suggests that there m ight be another phase where such defects are energetically favorable and proliferate. With a small number of the above type of defects, a small fraction of electrons are converted from localized to m obile states leading to a m etalwith a small concentration of m obile electrons. This is reminiscent of the two-uid picture [15], but now extended to accom-m odate orbital and charge order [20].

W e next address sim ilar instability issues in the context of the CE phase. First consider what happens when the CE phase is doped with carriers. As discussed above, experim entally there is a strong asym m etry between hole and electron doping. A coording to de Gennes's original argum ent [22], canted phases are expected for sm all doping (irrespective of their sign). It is known that the energy of the fully ferrom agnetic state crosses that of the CE state when extra electrons are added [8], but interm ediate canted phases have not been considered. They would naively lead to second-order transitions rather than rst-order. We have studied such canted phases and obtained the optimal canting angle as function of x close to 1/2. Sim ilarly to the discussion above in the context of the FI-CO phase, these hom ogeneous phases are in competition with inhom ogeneous phases where the added carriers are self-trapped by JT distortions. In fact, we nd that it is favorable to trap the added carriers at small c 1=2 x. This leads to an insulating un-canted CE phase (noted CE trapped in Fig. 3). On the electron-doped side (x < 1=2, Fig. 3), increasing c leads eventually to a canted m etallic phase (CFM) via a rstorder transition. This is because the JT energy gain due to trapping is linear in c, $E_{tr} = E_{JT}^{e;h} j c j$ (with $E_{JT}^{e;h}$ obtained by solving, for all g=t, the one-defect problem

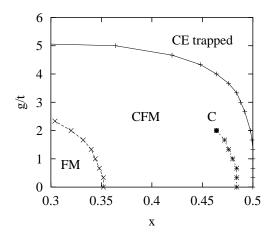


FIG.3: Phase diagram, g=t vs. doping, x $(J_{AF}S^2=t=0.15)$. CFM: canted CE state with distortions and charge-order (metallic). CE trapped: CE phase with extra carriers trapped in JT distortions (insulating). FM: ferrom agnetic metallic phase with no distortions. The upper curve is valid for x close enough to 0.5. C is a critical point ending a rst-order line between two canted states (with di erent canting angles).

mentioned above with one added carrier) [20], whereas the energy gain from canting is quadratic, E ca $(c)^{2}$ [22]. The latter loses for small c but wins for larger c. On the hole side, how ever, we nd that canted phases are never energetically favorable. The asym metry arises because of the nature of the CE ordering. Canting leads to a 2-d dispersion, with a large density of states at the bottom of the conduction band (for electron doping), whereas it gives a 3-d dispersion, with a vanishing DOS at the top of the valence band (for hole doping). Therefore, canting angles can indeed get large when electrons are added and compete e ectively against electron trapping. But when holes are added, canting angles are much smaller and the holes get trapped by JT distortions for g=t > 4. Hence the system remains insulating. Thus, our approach leads to an explanation for the asym m etry between particle and hole doping seen experim entally. It also helps us to understand why incom mensurate charge ordered CE type phases seem to be favoured on the hole doped side [20, 21].

An external magnetic-eld applied to the CE phase also promotes canting. Experimentally, as discussed earlier, a eld-induced insulator metal transition occurs at extremely small elds. To locate the transition in our theory, we minimize and compare the energies of various 8-sublattice structures in a eld, including the JTdistorted canted CE state, the undistorted canted state with the optim al (high) canting angle, etc. We indicate transition from a distorted canted CE phase (with the canting hardly changing the JT distortions) to an undistorted highly-canted (or FM) phase with increasing eld. At the transition, the system becomes metallic, there is a jump in the magnetization (Fig. 4), and an abrupt

relaxation of all the JT distortions to zero. The transition elds have very little to do with the magnetic energy scales, but are determ ined by the JT energies and depend strongly on q=t as is clear from Fig. 4. For $q=t^{>}$ 6:8, the ferrom agnetic state is insulating and no insulatormetal transition can be found, which puts a bound on the values of g=t that are appropriate. In the range $5:0 \leq g=t \leq 6:8$, which may be relevant for manganites (we need g=t > 5:0 to explain the existence of the A-CO phase [4] [see Fig. 1]), we nd an instability of the distorted canted CE phase towards creation of defects, which suggests that the eld-induced metallic phase in this case has the above m entioned two types of electrons. In all cases, there are abrupt changes in JT distortions at the transition, converting it from second-order (for progressive canting) to rst-order, in agreem ent with recent experiments [17, 18].

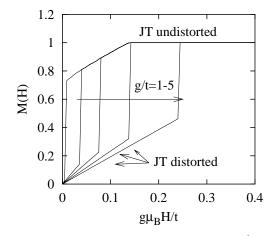


FIG.4: M agnetization vs. eld (g=t=15, $J_{AF}S^2$ =t=0.15). The rst-order transitions to an undistorted highly canted (or fully FM) m etallic phase is accompanied with a relaxation of the JT distortions.

However, the transition elds obtained in our calculations are too large compared to experiments. For instance, $g_B H_c$ 0:1t (Fig. 4), gives H_c 140 T (with t 0:2 eV). The discrepancy is connected with the overestimation of the charge gap in our model. Three effects need to be included to obtain a more realistic, reduced estimate for the charge gap. First, the niteness of the Hund's coupling, here taken to be in nite, which would allow for hopping even between sites with antialigned core spins; second, the cooperative nature of the JT phonons, causing sizeable distortions on the corner sites of the CE phase as well; and third, sm all second neighbour hopping. All of these would contribute to reducing the gap. Indeed, if we use the experimentally observed charge gap in place of the charge gap obtained in our model and then estimate the transition eld, we get num bers in good agreem ent with observations.

In conclusion, we have provided new theoretical insights into the physics of half-doped manganites. We suggest the existence of and competition between canting (ie., not full ferrom agnetism , which could be checked by neutron di raction) induced m etallicity and inhom ogeneity arising from the trapping of carriers by JT defects. It explains several features of the doping-induced (e.g. the particle-hole asymmetry) and eld-induced insulatormetal transition. These ideas suggest a new two-uid modelwith localized and mobile electrons, which extends the work of ref. 15 to include orbital and charge order, which when treated with more sophisticated methods such as DM FT can yield a satisfactory and complete theory of doped manganites including the regime near half-doping.

O.C. would like to thank G.Bouzerar, T.Chatterji, G. Jackeli, D.Khomskii, Y.Motome, H.Nojiri and T.Ziman for stimulating discussions. OC and HRK acknowledge nancial support from FCPAR, grant 2404-1.

- [L] see Y. Tokura, ed. Cobssal M agnetoresistance O xides
 (Gordon and Breach, New York, 2000); M. B. Salamon,
 M. Jaime, Rev. M od. Phys. 73, 583 (2001); E. D agotto,
 T. Hotta and A. Moreo, Physics Reports. 344, 1 (2001).
- [2] E.O.W ollan and W.C.Koehler, Phys. Rev. 100, 545 (1955).
- [3] J.B.Goodenough, Phys. Rev. 100, 564 (1955).
- [4] H.Kawano et al, Phys. Rev. Lett. 78, 4253 (1997); Phys. Rev. B 67, 174422 (2003).
- [5] F.M illange, S. de Brion, and G. Chouteau, Phys. Rev. B 62, 5619 (2000).
- [6] S.K.M ishra, R.Pandit, and S.Satpathy, Phys. Rev. B 56, 2316 (1997).
- [7] P.G.Radaelli et al, Phys.Rev.Lett. 75, 4488 (1995); Phys.Rev.B 55, 3015 (1997).
- [8] J van den Brink, G.Khaliullin, and D.Khomskii, Phys. Rev.Lett. 83, 5118 (1999).
- [9] G. Jackeli, N. B. Perkins, and N. M. Plakida, Phys. Rev. B 62, 372 (2000).
- [10] S. Fratini, D. Feinberg, and M. Grilli, Eur. Phys. J. B 22, 157 (2001).
- [11] Z.Popovic and S.Satpathy, Phys.Rev.Lett.88, 197201
 (2002).
- [12] T.Hotta, A.-L.Malvezzi, E.Dagotto, Phys. Rev. B 62, 9432 (2000); S.Yunoki, T.Hotta, E.Dagotto, Phys. Rev. Lett. 84, 3714 (2000).
- [13] Y.Tom ioka et al., Phys. Rev. Lett. 74, 5108 (1995); Y. Tokura et al., ibid. 76, 3184 (1996); Y.Tokura and Y. Tom ioka, J.M agn. M agn. M ater. 200, 1 (1999).
- [14] H.Aliaga et al, Phys. Rev. B 68, 104405 (2003).
- [15] T.V.Ramakrishnan et al, Phys. Rev. Lett. 92, 157203 (2004).
- [16] M.Roy et al, Phys. Rev. B 58, 5185 (1998).
- [17] T.A.Tyson et al, Phys.Rev.B 70, 024410 (2004).
- [18] H.Nojiri, private communication.
- [19] V.Brouet et al, Phys.Rev.Lett.82,2131 (1999); Phys. Rev.B 66,155123 (2002).
- [20] D etails will be given elsewhere.
- [21] S.M ori, C.H.Chen, and S.W. Cheong, Nature (London) 392, 473 (1998); J.C.Loudon et al., cond-m at/0308581; L.Brey, Phys. Rev. Lett. 92, 127202 (2004).
- [22] P.-G. de Gennes, Phys. Rev. 118, 141 (1960).